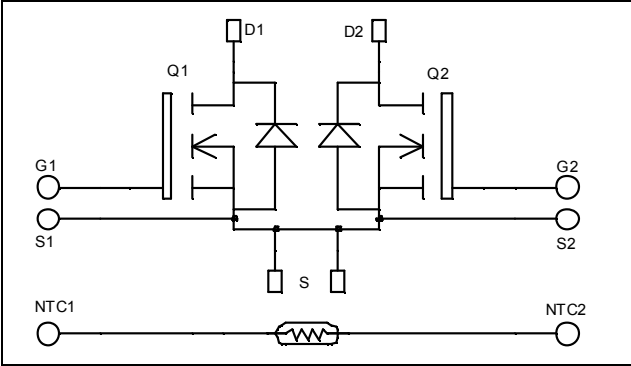


Dual Common Source MOSFET Power Module

$V_{DSS} = 1200V$
 $R_{DSon} = 290m\Omega \text{ typ @ } T_j = 25^\circ C$
 $I_D = 34A \text{ @ } T_c = 25^\circ C$

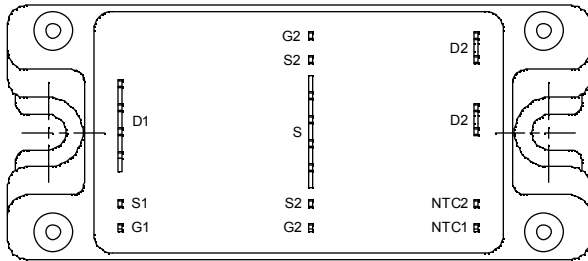


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	136	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	348	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	22	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 1200\text{V}$			350	μA
		$V_{GS} = 0\text{V}, V_{DS} = 1000\text{V}$	$T_j = 25^\circ\text{C}$		1500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 17\text{A}$		290	348	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		10.3		nF
C_{oss}	Output Capacitance			1.54		
C_{rss}	Reverse Transfer Capacitance			0.26		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 600\text{V}$ $I_D = 34\text{A}$		374		nC
Q_{gs}	Gate – Source Charge			48		
Q_{gd}	Gate – Drain Charge			240		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15\text{V}$ $V_{Bus} = 800\text{V}$ $I_D = 34\text{A}$ $R_G = 2.5\Omega$		20		ns
T_r	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			160		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 800\text{V}$ $I_D = 34\text{A}, R_G = 2.5\Omega$		1980		μJ
E_{off}	Turn-off Switching Energy			1371		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 800\text{V}$ $I_D = 34\text{A}, R_G = 2.5\Omega$		3131		μJ
E_{off}	Turn-off Switching Energy			1714		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$			34	A
		$T_c = 80^\circ\text{C}$			25	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -34\text{A}$			1.3	V
dv/dt	Peak Diode Recovery ①				10	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -34\text{A}; V_R = 600\text{V}$		1291		ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 200\text{A}/\mu\text{s}$		58		μC

① dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -34\text{A} \quad di/dt \leq 700\text{A}/\mu\text{s} \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

Thermal and package characteristics

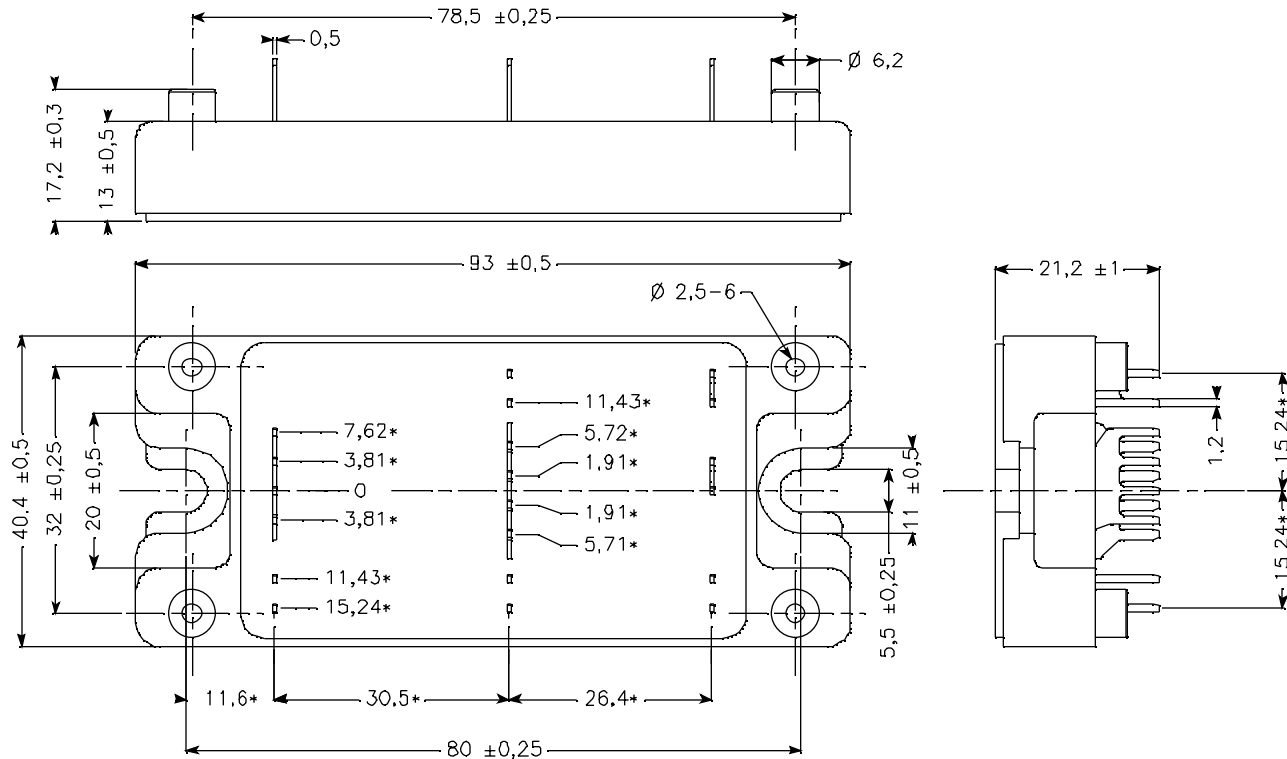
Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance			0.16	°C/W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight			160		g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

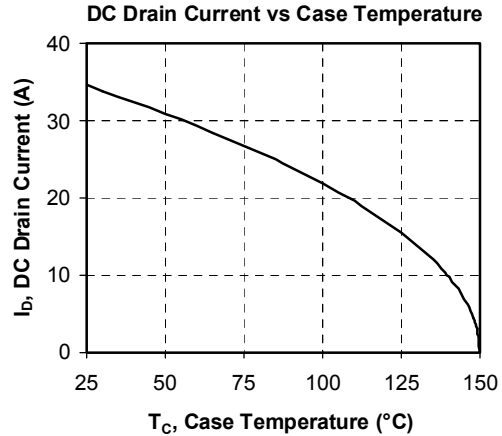
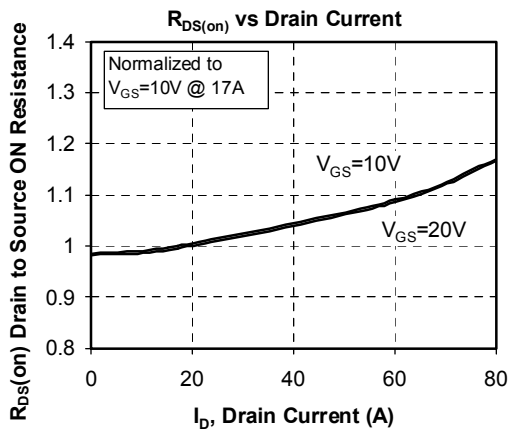
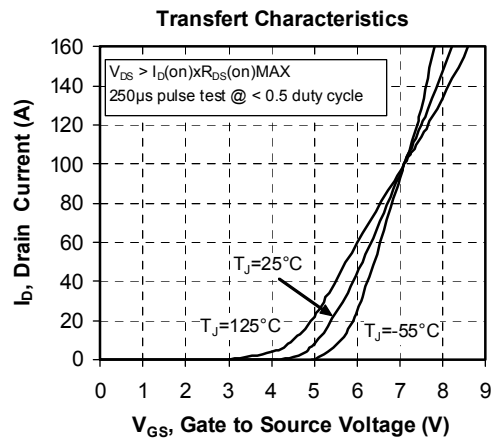
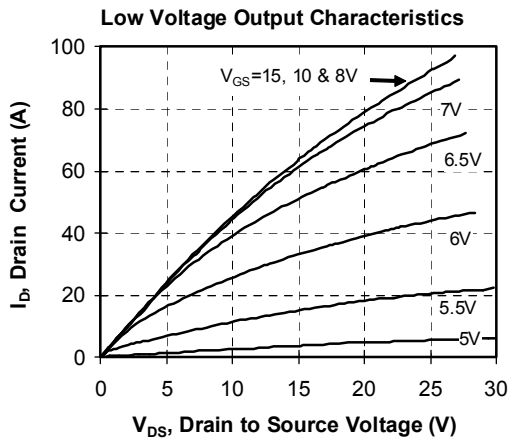
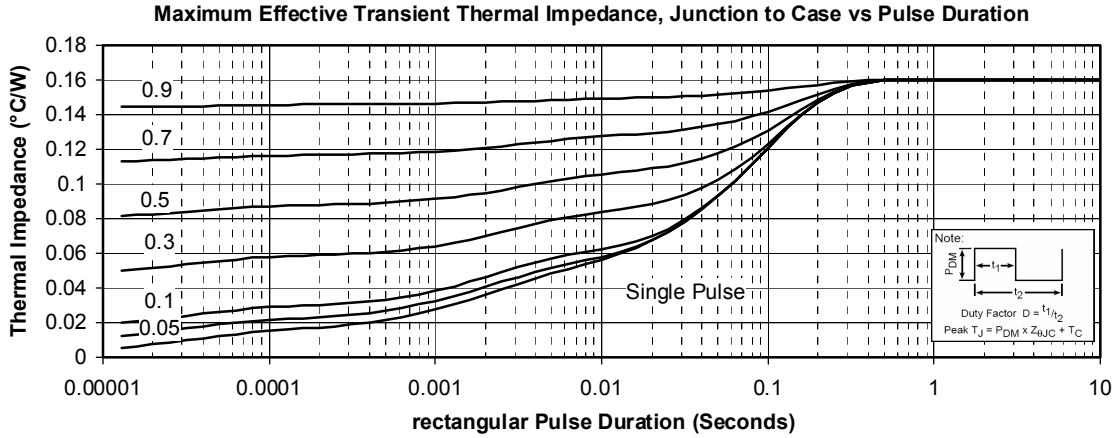
Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

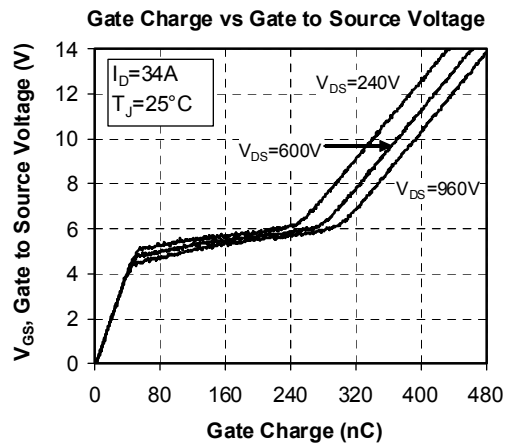
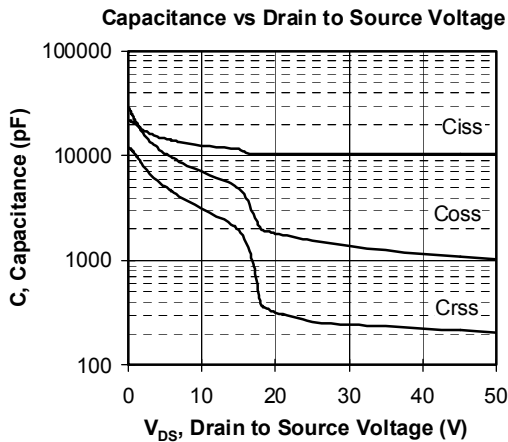
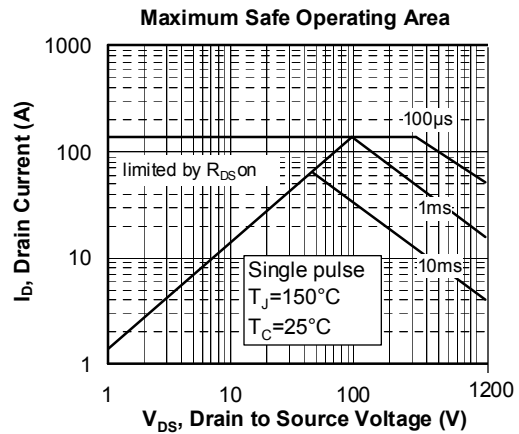
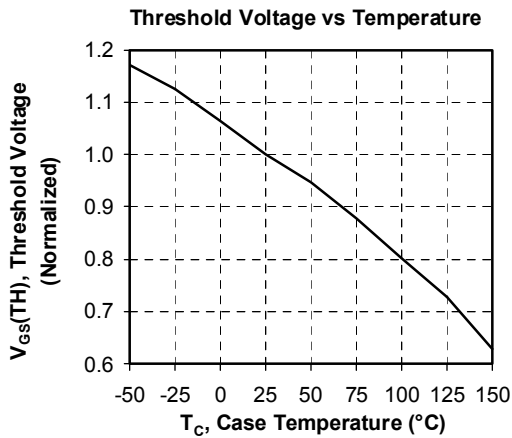
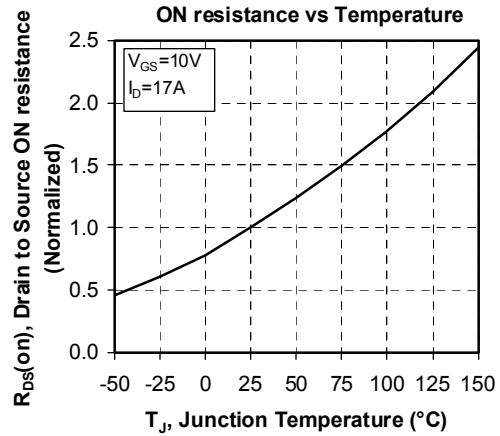
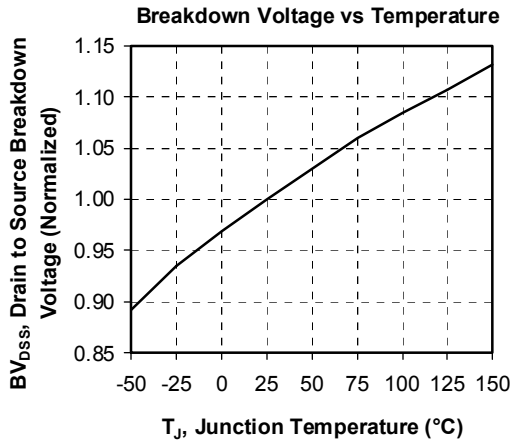
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

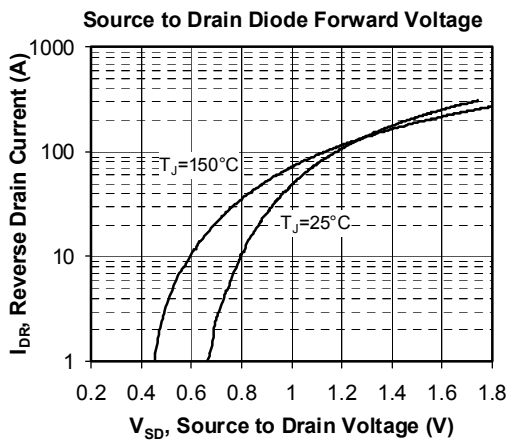
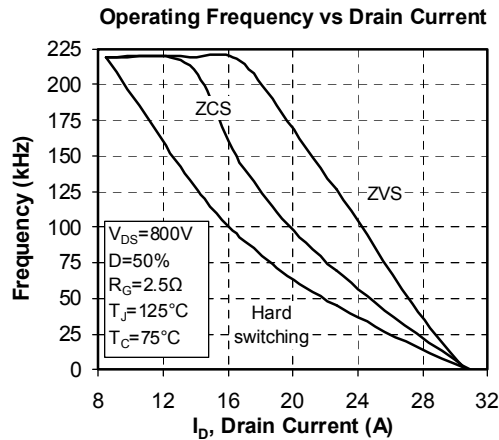
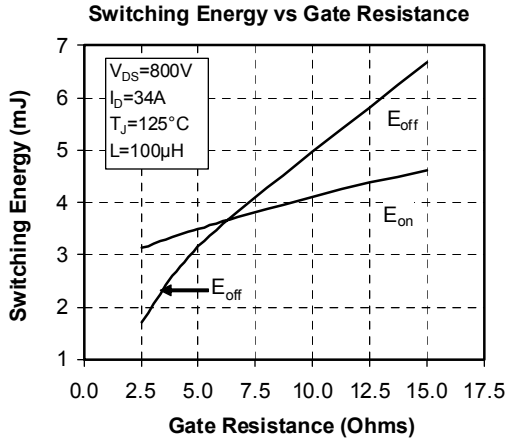
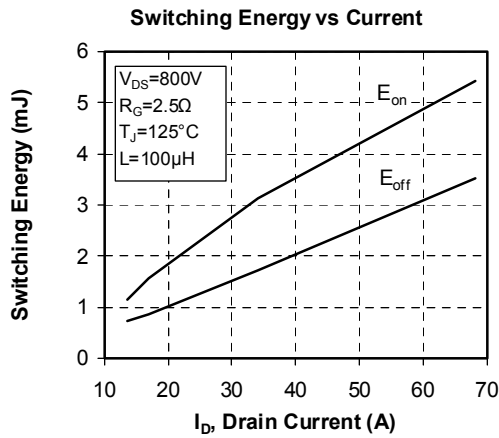
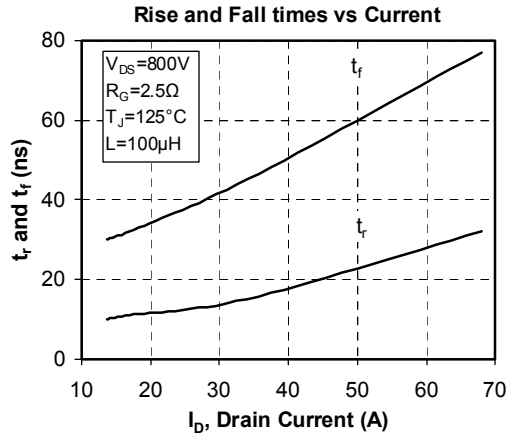
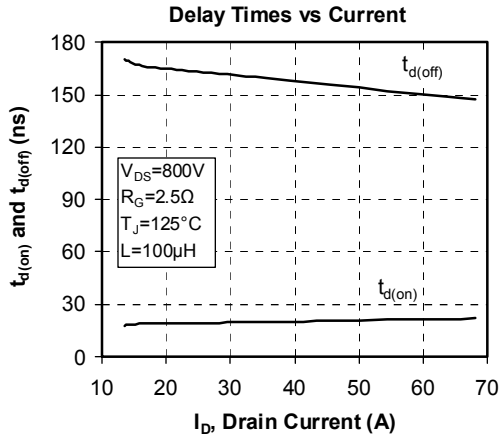
T: Thermistor temperature
 R_T: Thermistor value at T

SP4 Package outline (dimensions in mm)

 ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS: $\boxed{\oplus \ominus 0.1}$

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve






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